

| INFORMATION DISCLOSURE CITATION PTO-1449 | | | Atty. Docket No. NTI-703CIP3 Applicant PANG, Linyong Filing Date 7/11/03 | | Serial No. 19 618 816 Group 2825 | |
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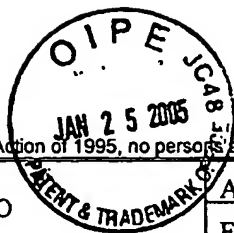
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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary) | | | | Application Number | | 10/618,816 | | |
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| | | | | Examiner: Unknown | | GROUP: 2825 | | |
| Sheet | 1 | of | 1 | Attorney Docket Number | | NTI-703-1P1P | | |
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